

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sei-Hyung Ryu

Serial No.: To Be Assigned

Filed: Concurrently Herewith

For: VERTICAL JFET LIMITED SILICON CARBIDE POWER METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS AND METHODS OF
FABRICATING VERTICAL JFET LIMITED SILICON CARBIDE METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Date: October 30, 2003

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

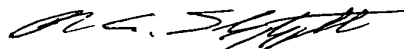
Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,



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Candi L. Riggs

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| | | | | Applicants: Sei-Hyung Ryu | | | |
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